09/888419

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device is constructed by stacking an n-cladding layer, an n-optical guide layer, an MQW active layer, a p-cap layer, a p-optical guide layer, a p-cladding layer, an n-current blocking layer, and a p-contact layer in this order on one surface of a transparent substrate. A p electrode is formed on a predetermined region of the p-contact layer. An n electrode having a projected shape is formed on the other surface of the transparent substrate. In this case, a portion, where a projection of the n electrode is arranged, of the device corresponds to the front (a surface on the side of laser light emission) thereof.

09888419 - 062700